

# MOSFET - Power, Single N-Channel, DFNW8 80 V, 2 mΩ, 229 A



ON Semiconductor®

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## NTMTS002N08MC

### Features

- Small Footprint (8x8 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	80	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 20$	V	
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	229	A
			$P_D$	208	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	29	A
			$P_D$	3.3	W
Pulsed Drain Current	$T_C = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	$I_{DM}$	3577	A	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 29 \text{ A}, L = 3 \text{ mH}$ )		$E_{AS}$	1261.5	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

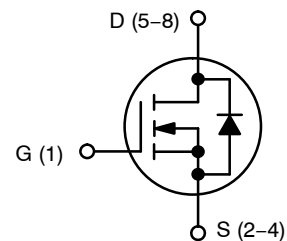
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

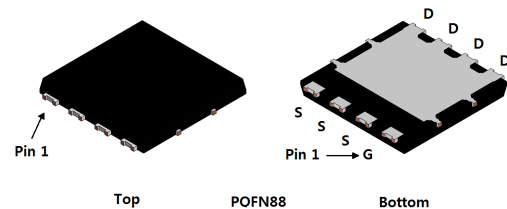
Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State (Note 2)	$R_{\theta JC}$	0.6	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	38	$^\circ\text{C}/\text{W}$

1. Surface-mounted on FR4 board using a 1 in<sup>2</sup> pad size, 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	2 mΩ @ 10 V	229 A
	5.1 mΩ @ 6 V	

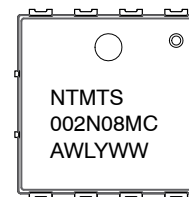


N-CHANNEL MOSFET



DFNW8  
CASE 507AP

### MARKING DIAGRAM



NTMTS002N08MC = Device Code  
A = Assembly Location  
WL = 2-digit Wafer Lot Code  
Y = Year Code  
WW = Work Week Code

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NTMTS002N08MC

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$ , ref to $25^\circ\text{C}$		68		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25^\circ\text{C}$		1	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA

## ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 540\ \mu\text{A}$	2.0	2.7	4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 540\ \mu\text{A}$ , ref to $25^\circ\text{C}$		-7.9		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 90\text{ A}$		1.3	2.0	m $\Omega$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 6\text{ V}, I_D = 48\text{ A}$		1.8	5.1	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{ V}, I_D = 90\text{ A}$		214		S
Gate Resistance	$R_G$	$T_A = 25^\circ\text{C}$		0.8		$\Omega$

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$		6350	8900	pF
Output Capacitance	$C_{OSS}$			2100	3000	
Reverse Transfer Capacitance	$C_{RSS}$			93	130	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}; I_D = 90\text{ A}$		89	125	nC
Threshold Gate Charge	$Q_{G(TH)}$			16	22	
Gate-to-Source Charge	$Q_{GS}$			25		
Gate-to-Drain Charge	$Q_{GD}$			19		
Output Charge	$Q_{OSS}$			117		
Sync Charge	$Q_{sync}$			72		
Plateau Voltage	$V_{plateau}$			4		

## SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 40\text{ V}, I_D = 90\text{ A}, R_G = 6\ \Omega$		26		ns
Rise Time	$t_r$			20		
Turn-Off Delay Time	$t_{d(OFF)}$			65		
Fall Time	$t_f$			29		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 2\text{ A}$		0.7	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 90\text{ A}$		0.8	1.3	
Reverse Recovery Time	$t_{RR}$	$I_F = 45\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		34	54	ns
Reverse Recovery Charge	$Q_{RR}$			71	114	
Reverse Recovery Time	$t_{RR}$	$I_F = 45\text{ A}, di/dt = 1000\text{ A}/\mu\text{s}$		27	43	nC
Reverse Recovery Charge	$Q_{RR}$			177	283	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

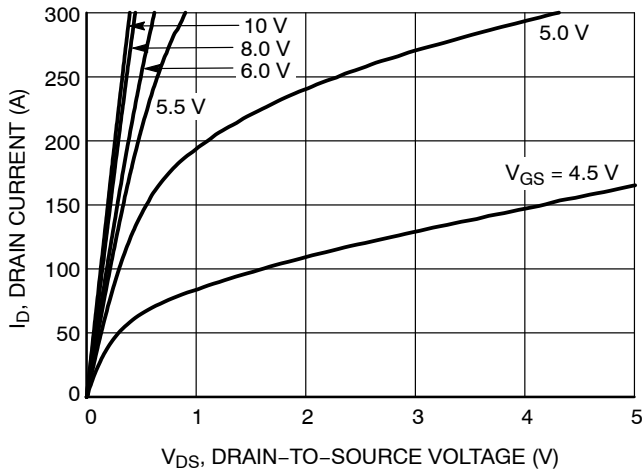


Figure 1. On-Region Characteristics

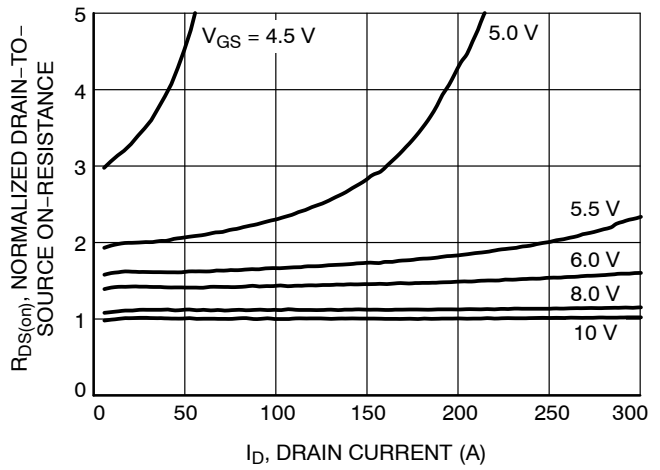


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

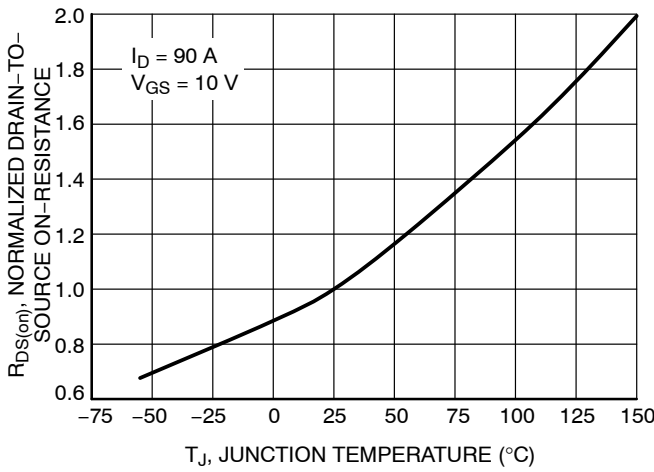


Figure 3. Normalized On Resistance vs. Junction Temperature

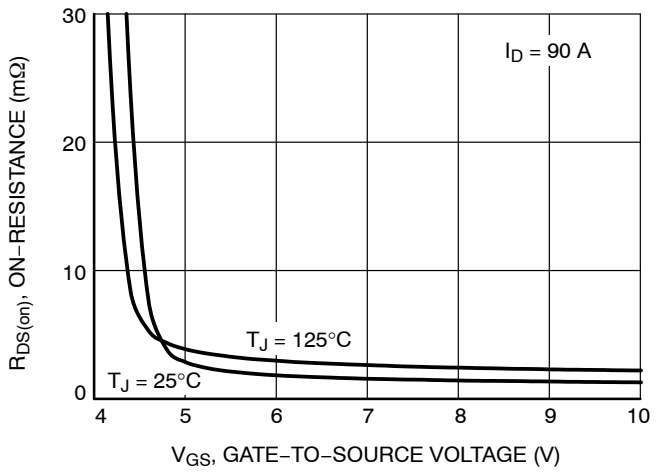


Figure 4. On-Resistance vs. Gate-to-Source Voltage

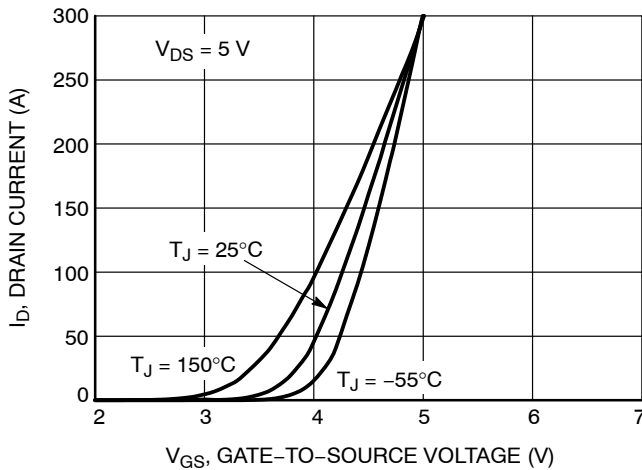


Figure 5. Transfer Characteristics

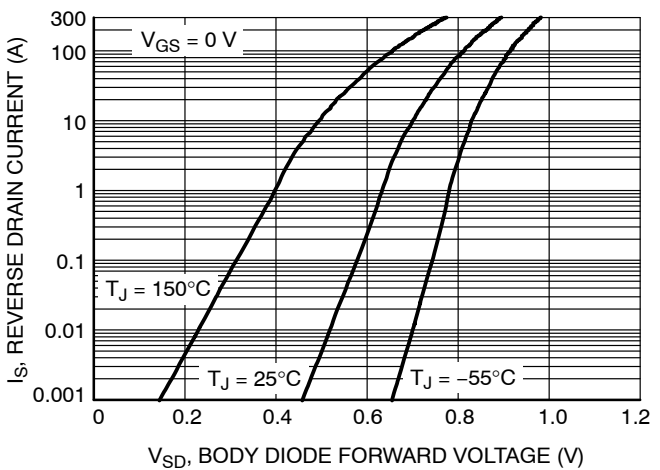


Figure 6. Source-to-Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS

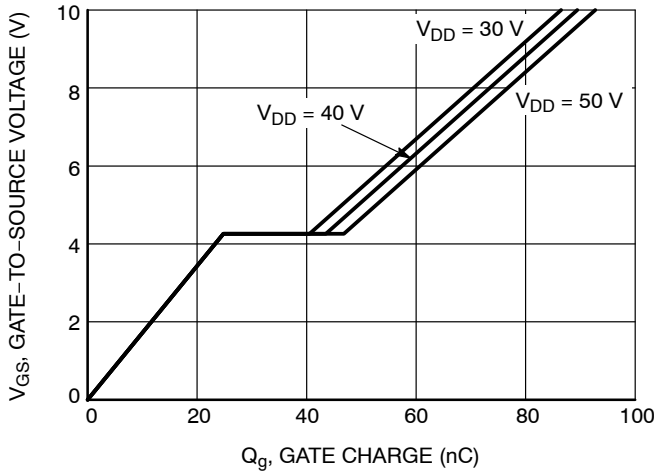


Figure 7. Gate Charge Characteristics

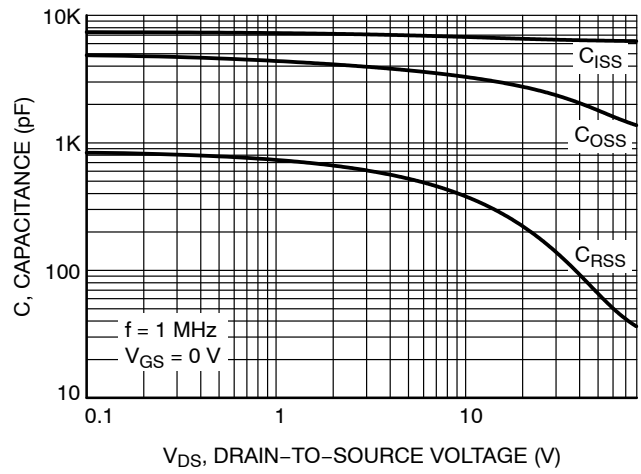


Figure 8. Capacitance vs. Drain-to-Source Voltage

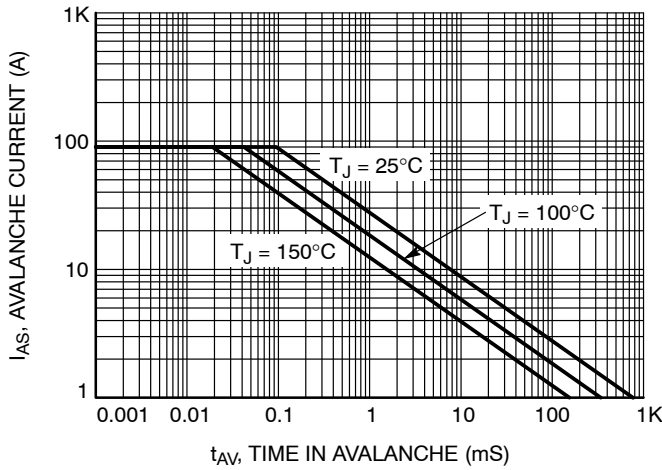


Figure 9. Unclamped Inductive Switching Capability

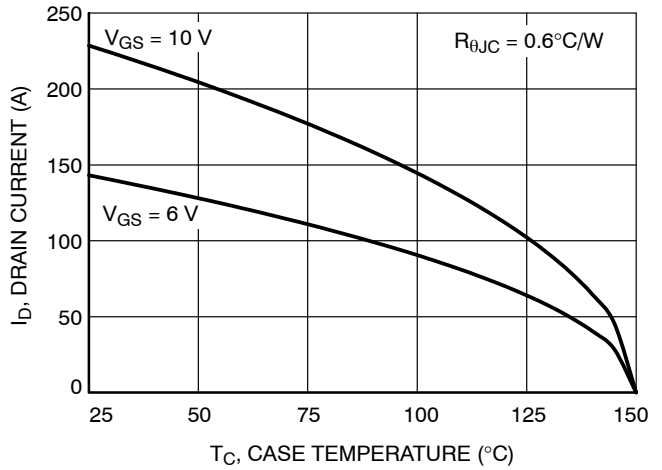


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

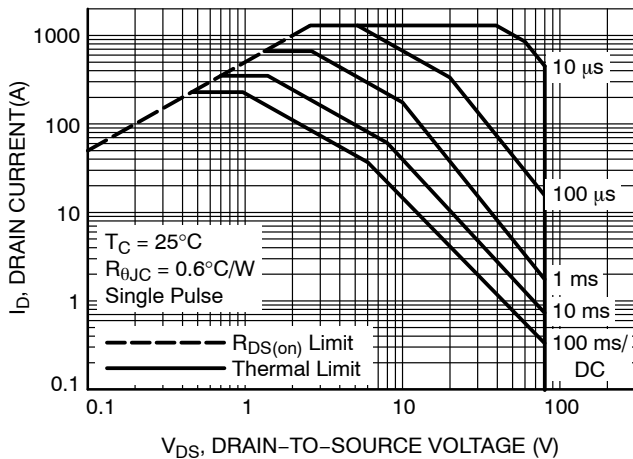


Figure 11. Forward Biased Safe Operating Area

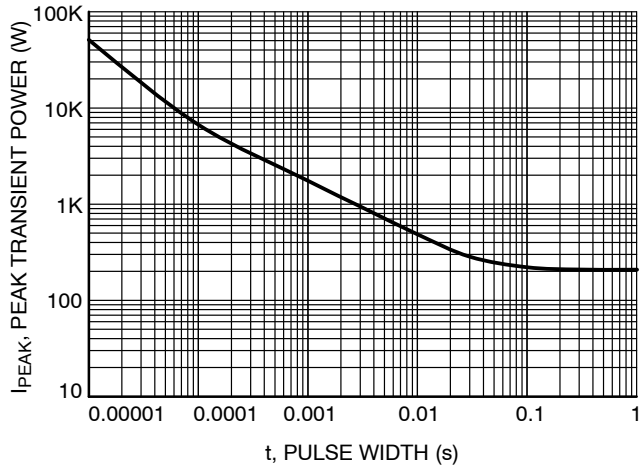


Figure 12. Single Pulse Maximum Power Dissipation

# NTMTS002N08MC

## TYPICAL CHARACTERISTICS

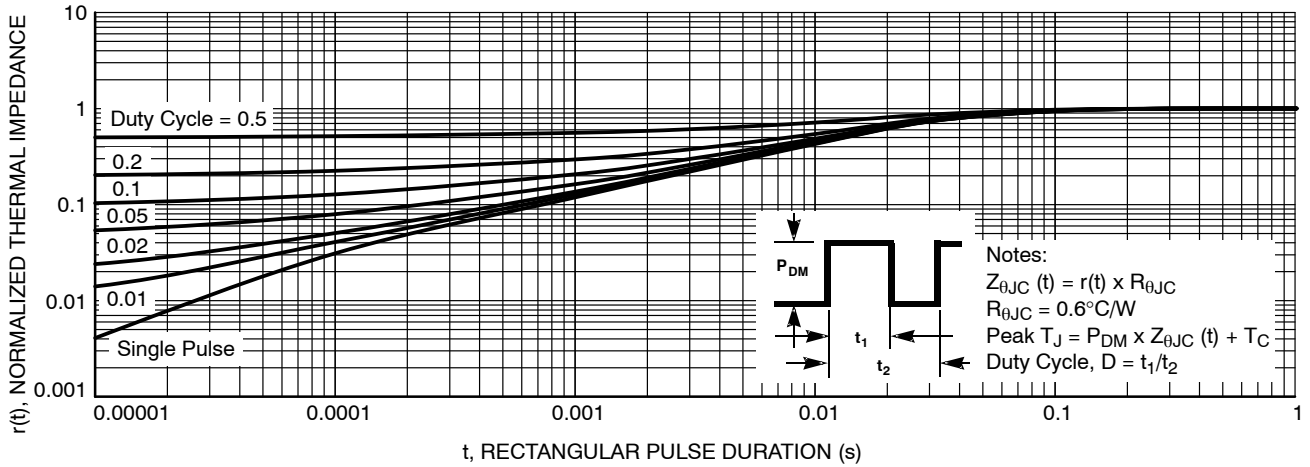


Figure 13. Transient Thermal Impedance

### DEVICE ORDERING INFORMATION

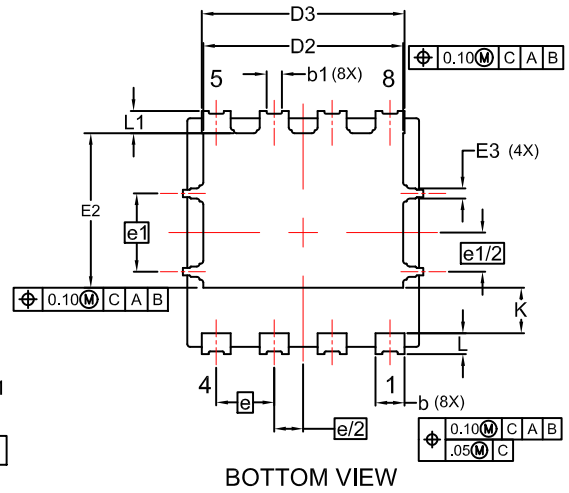
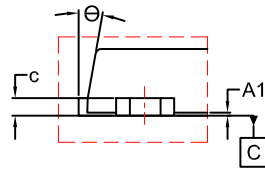
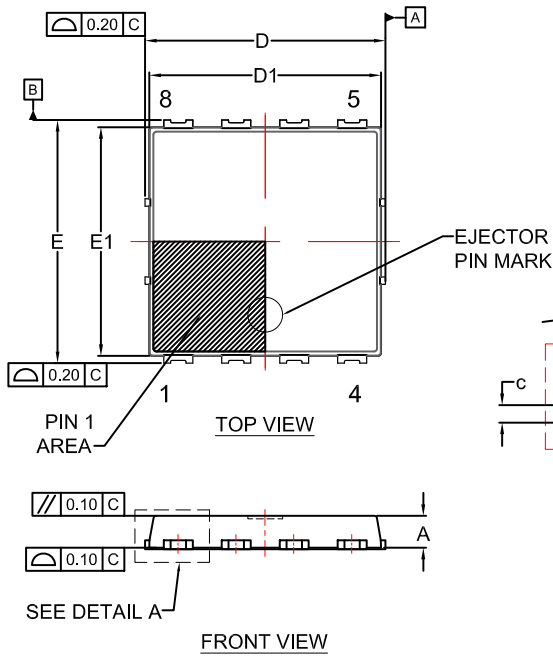
Device	Marking	Package	Shipping†
NTMTS002N08MC	NTMTS 002N08MC	DFNW8 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTMTS002N08MC

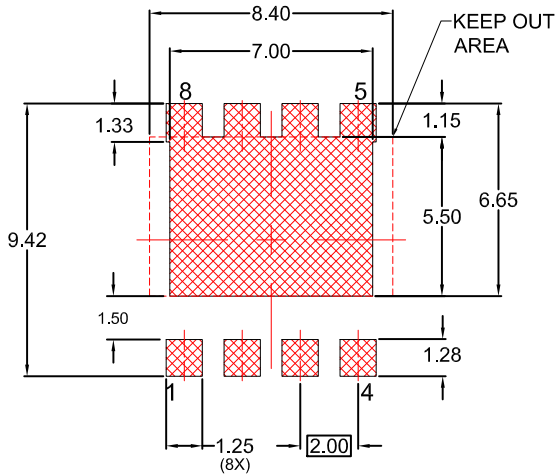
## PACKAGE DIMENSIONS

DFNW8 8.3x8.4, 2P  
CASE 507AP  
ISSUE B




**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.10	1.20
A1	0.00	---	0.05
b	0.90	1.00	1.10
b1	0.43	0.53	0.63
c	0.23	0.28	0.33
D	8.20	8.30	8.40
D1	7.90	8.00	8.10
D2	6.80	6.90	7.00
D3	6.90	7.00	7.10
E	8.30	8.40	8.50
E1	7.80	7.90	8.00
E2	5.24	5.34	5.44
E3	0.25	0.35	0.45
e	2.00 BSC		
e/2	1.00 BSC		
e1	2.70 BSC		
e1/2	1.35 BSC		
K	1.50	1.57	1.70
L	0.64	0.74	0.84
L1	0.67	0.77	0.87
$\theta$	0°	---	12°

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